# NCE N-Channel Super Trench Power MOSFET

## Description

The NCEP1505S uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and $Q_g$. This device is ideal for high-frequency switching and synchronous rectification.

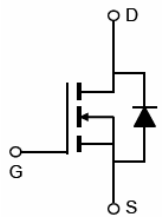
## General Features

- $V_{DS}$ =150V,$I_D$ =5.1A
  $R_{DS(ON)}$ < 65mΩ @ $V_{GS}$=10V ( Typ: 55mΩ)
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature

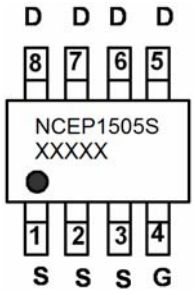
## Application

- DC/DC converters and Off-Line UPS
- High Voltage Synchronous Rectifier
- Hard switched and high frequency circuits
- Uninterruptible power supply

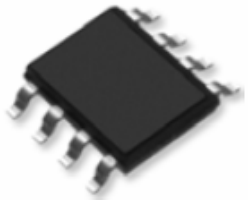
***100% ΔVds TESTED!***




**Schematic diagram**




**Marking and pin assignment**



**SOP-8 top view**

## Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|---|---|---|---|---|---|
| NCEP1505S | NCEP1505S | SOP-8 | Ø330mm | 12mm | 4000 units |

## Absolute Maximum Ratings ($T_A$=25℃unless otherwise noted)

| Parameter | | Symbol | Limit | Unit |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DS}$ | 150 | V |
| Gate-Source Voltage | | $V_{GS}$ | ±20 | V |
| Drain Current-Continuous | | $I_D$ | 5.1 | A |
| Drain Current-Continuous($T_C$=100℃) | | $I_D$ (100℃) | 3.6 | A |
| Pulsed Drain Current(Note 1) | | $I_{DM}$ | 20 | A |
| Single pulse avalanche energy (Note 5) | | $E_{AS}$ | 60 | mJ |
| Maximum Power Dissipation | $T_C$ = 25 °C | $P_D$ | 5 | W |
| | $T_A$ = 25 °C | | 3 | W |
| Operating Junction and Storage Temperature Range | | $T_J$,$T_{STG}$ | -55 To 150 | ℃ |

## Thermal Characteristic

| | | | |
|---|---|---|---|
| Thermal Resistance, Junction-to-Ambient(Note 2) | $R_{\theta JA}$ | 41.7 | ℃/W |
| Thermal Resistance, Junction-to-Case(Note 2) | $R_{\theta JC}$ | 25 | |

## Electrical Characteristics ($T_A$=25℃unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$=0V $I_D$=250μA | 150 | - | - | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$=150V,$V_{GS}$=0V | - | - | 1 | μA |
| Gate-Body Leakage Current | $I_{GSS}$ | $V_{GS}$=±20V,$V_{DS}$=0V | - | - | ±100 | nA |
| **On Characteristics** (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$=$V_{GS}$,$I_D$=250μA | 2.5 | 3.3 | 4.5 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}$=10V, $I_D$=5.1A | - | 55 | 65 | mΩ |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$=5V,$I_D$=5.1A | - | 12.5 | - | S |
| **Dynamic Characteristics** (Note4) | | | | | | |
| Input Capacitance | $C_{lss}$ | $V_{DS}$=75V,$V_{GS}$=0V, F=1.0MHz | - | 618 | 850 | PF |
| Output Capacitance | $C_{oss}$ | | - | 81 | 105 | PF |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 6.5 | 9 | PF |
| **Switching Characteristics** (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}$=75V, $I_D$=5.1A $V_{GS}$=10V,$R_G$=3Ω | - | 12.8 | 14 | nS |
| Turn-on Rise Time | $t_r$ | | - | 1.4 | 8.5 | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 12.5 | 21 | nS |
| Turn-Off Fall Time | $t_f$ | | - | 2.5 | 8.0 | nS |
| Total Gate Charge | $Q_g$ | $V_{DS}$=75V,$I_D$=5.1A, $V_{GS}$=10V | - | 12.8 | 18.0 | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | 5 | | nC |
| Gate-Drain Charge | $Q_{gd}$ | | - | 3.6 | | nC |
| **Drain-Source Diode Characteristics** | | | | | | |
| Diode Forward Voltage (Note 3) | $V_{SD}$ | $V_{GS}$=0V,$I_S$=5.1A | - | - | 1.2 | V |
| Diode Forward Current (Note 2) | $I_S$ | | - | - | 5.1 | A |
| Reverse Recovery Time | $t_{rr}$ | $T_J$ = 25°C, $I_F$ = $I_S$ di/dt = 100A/μs (Note3) | - | 58 | 95 | nS |
| Reverse Recovery Charge | Qrr | | - | 69 | 110 | nC |

Notes:

**1.** Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A$ =25°C. The value in any given application depends on the user's specific board design.

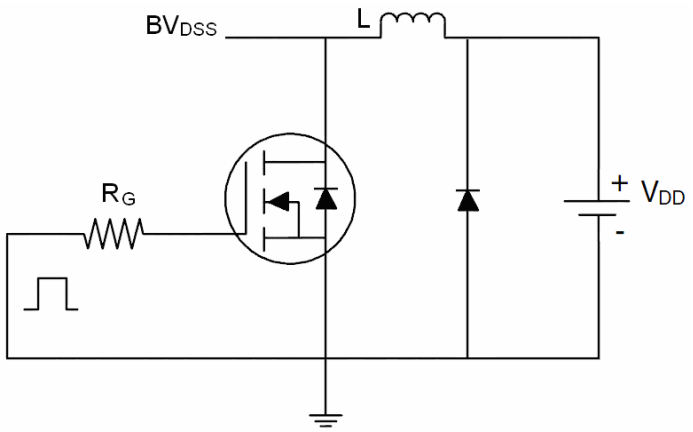
**3.** Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

**4.** Guaranteed by design, not subject to production

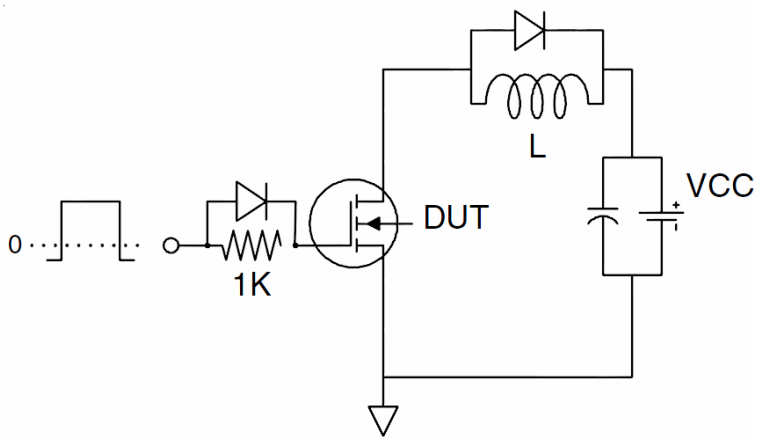
5. EAS condition : Tj=25℃,$V_{DD}$=50V,$V_G$=10V,L=0.5mH,Rg=25Ω

## Test Circuit

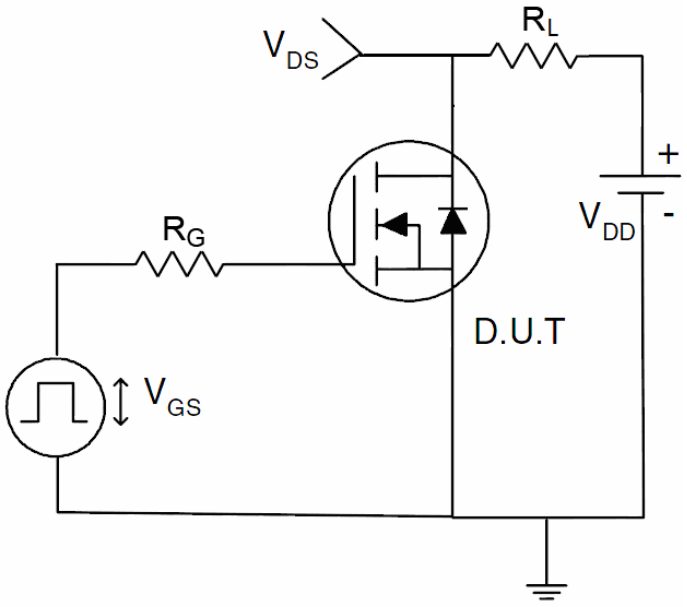
### 1) $E_{AS}$ test Circuit




### 2) Gate charge test Circuit




### 3) Switch Time Test Circuit



## Typical Electrical and Thermal Characteristics (Curves)

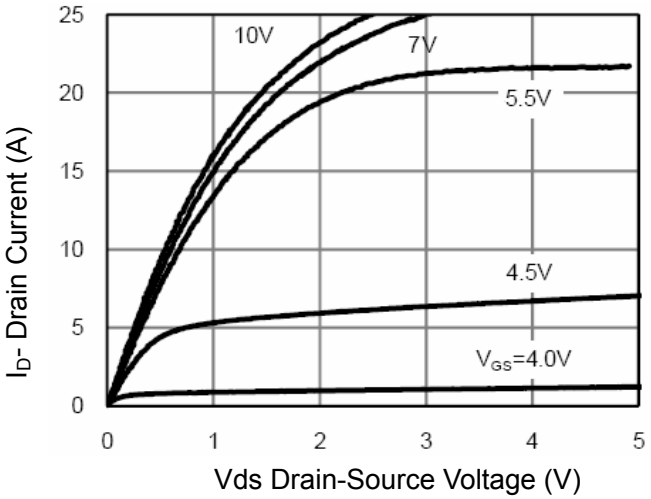



**Figure 1 Output Characteristics**

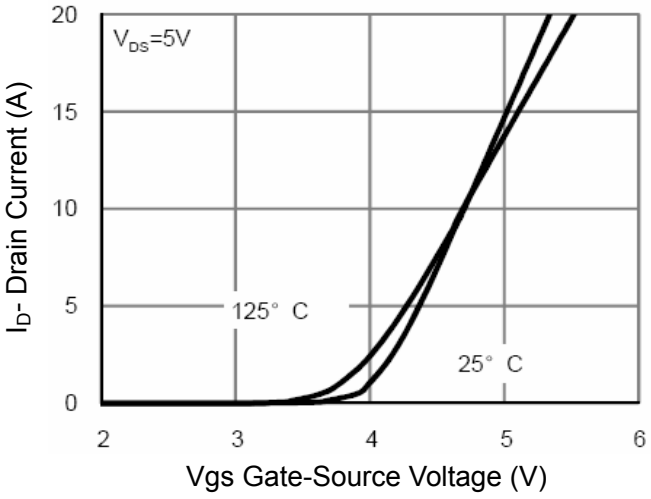



**Figure 2 Transfer Characteristics**

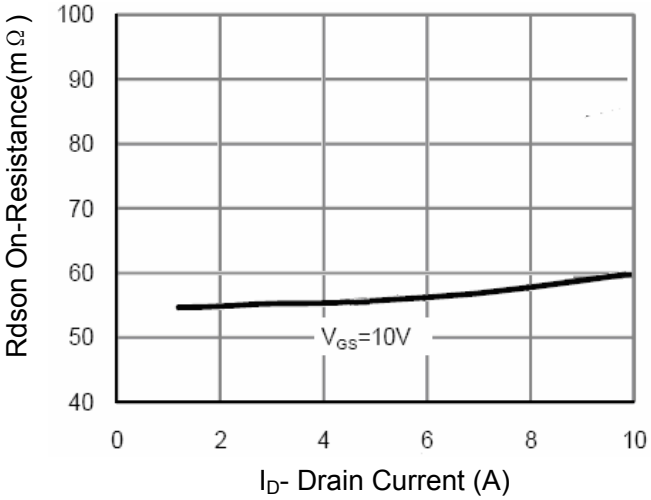



**Figure 3 Rdson- Drain Current**

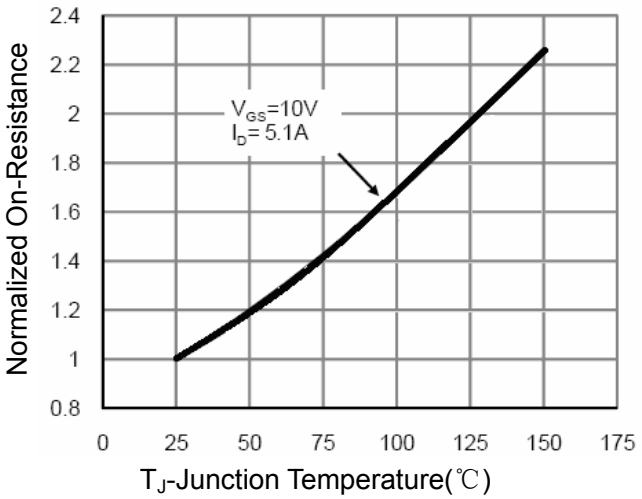



**Figure 4 Rdson-JunctionTemperature**

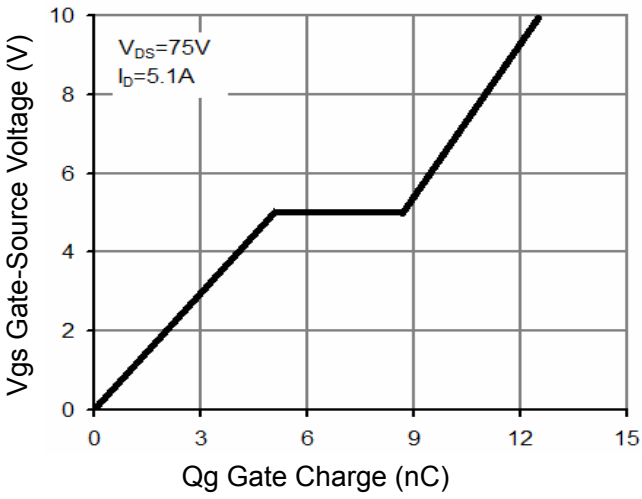



**Figure 5 Gate Charge**

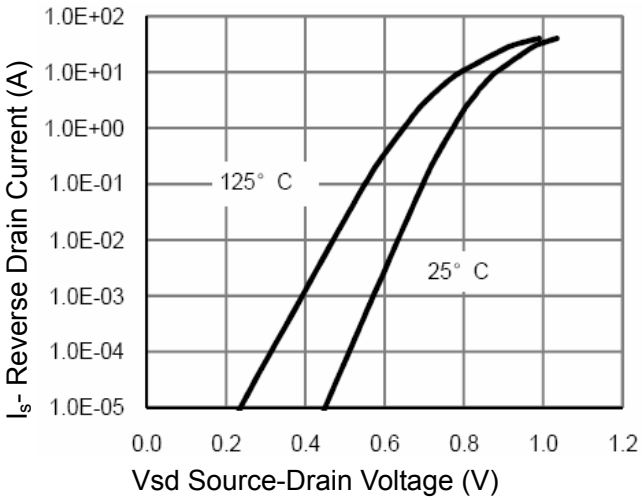



**Figure 6 Source- Drain Diode Forward**

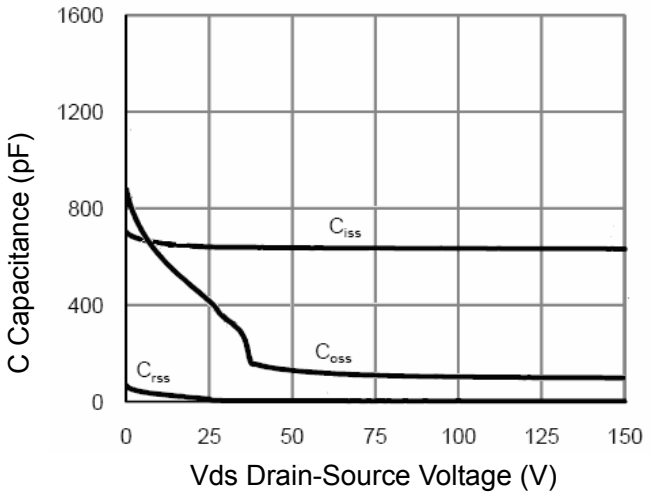



**Figure 7 Capacitance vs Vds**

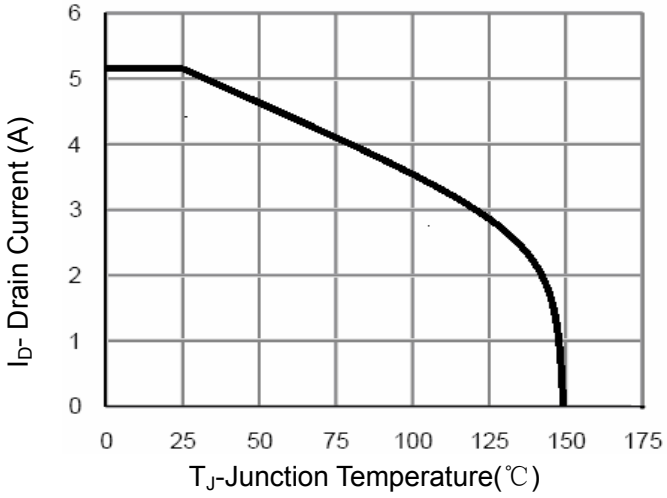



**Figure 9 Current De-rating**

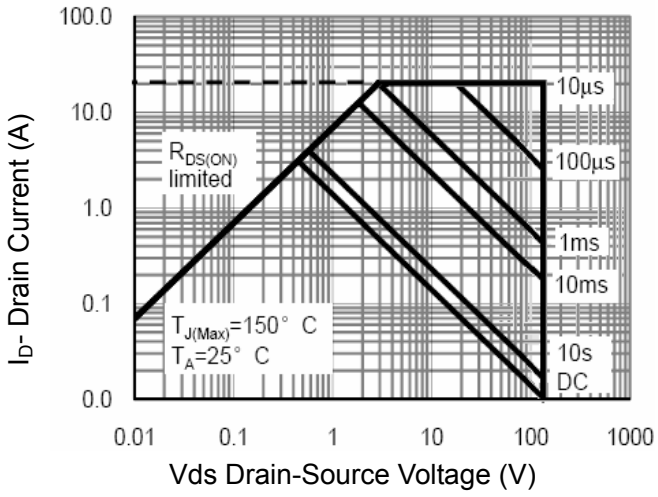



**Figure 8 Safe Operation Area**

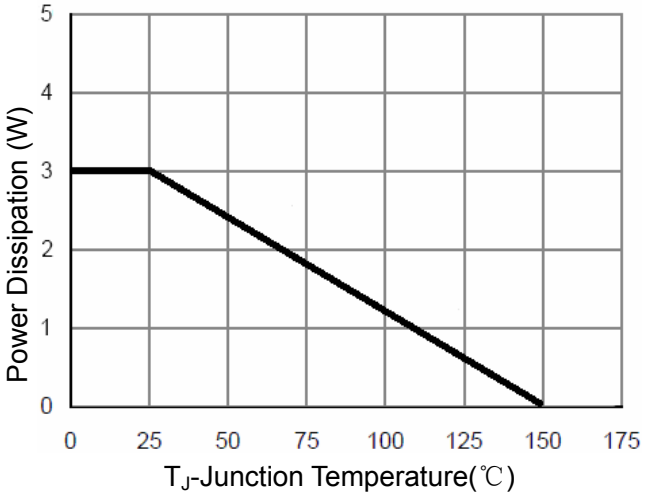



**Figure 10 Power De-rating**

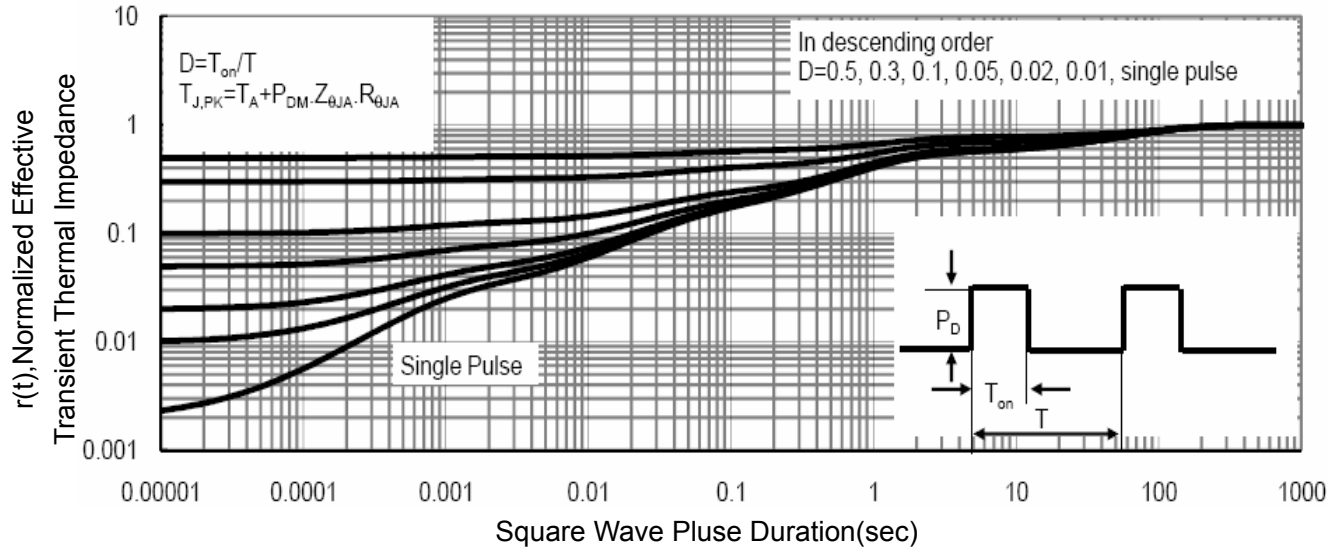
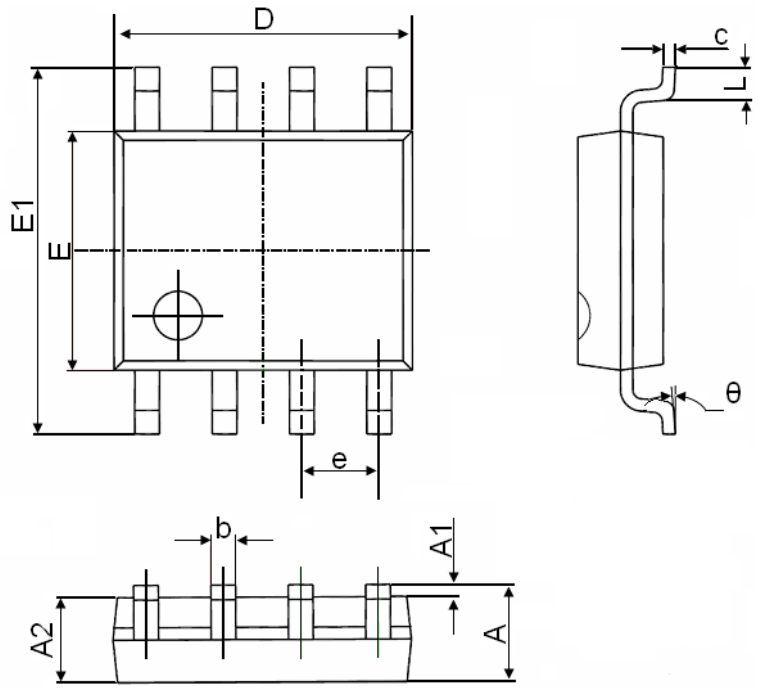


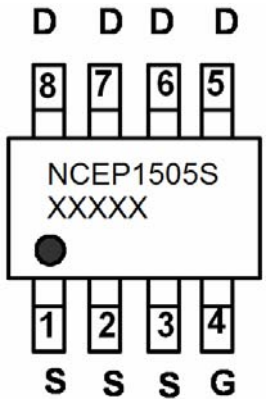

**Figure 11 Normalized Maximum Transient Thermal Impedance**

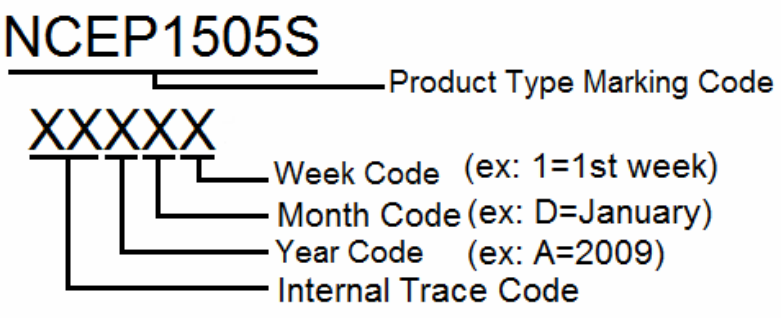
## SOP-8 Package Information




| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|---|---|---|---|---|
| | Min. | Max. | Min. | Max. |
| A | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| c | 0.170 | 0.250 | 0.006 | 0.010 |
| D | 4.700 | 5.100 | 0.185 | 0.200 |
| E | 3.800 | 4.000 | 0.150 | 0.157 |
| E1 | 5.800 | 6.200 | 0.228 | 0.244 |
| e | 1.270(BSC) | | 0.050(BSC) | |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |

## SOP-8 Part Marking



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